

BALLROOM

OF1-1: A Monolithic GaAs PIN Switch Network for a 77 GHz Automotive Collision Avoidance Radar
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OF1-2: Temperature Analysis and On-Chip Compensation for an UHF VCO
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OF1-3: Multilayer Passive Components for Uniplanar Si/SiGe MMICs
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OF1-4: Analysis of Ground Bond Wire Arrays for RFICs
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OF1-5: Accurate Passive Component Models in Coplanar Waveguide for 50 GHz MMICs
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OF1-6: Alignment Tolerant Stripline Directional Couplers
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OF1-7: Experimental Study of Wideband Uniplanar Phase Inverters for MICs
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OF1-8: Theory on Rotated Excitation of a Circular Dual-Mode Resonator and Filter
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OF1-9: Design Methodology for Multilayer Coupled Line Filters
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OF1-10: A Miniaturized Monolithic Dual Band Filter Using Ceramic Lamination Technique
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OF1-11: Bandpass and Bandstop Filters Using Dominant TM01-Mode Dielectric Rod Resonators
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OF1-12: Modeling of Conductor Loaded Resonators and Filters in Rectangular Enclosures
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OF1-13: Tapped-Line Interdigital Filter Equivalent Circuits
 C. Ernst, V. Postoyalko, Micro. & Terahertz Tech. Group, Dept. of EEE, Univ. of Leeds, Leeds, England

OF1-14: The Design of Band-Pass Filters Made of Both Dielectric and Coaxial Resonators
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OF1-15: A Monolithic Active Notch Tunable Filter Based on the Gyrator Principle
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OF1-16: Comparative Performance of Three Different CPW Bandpass Filters
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OF1-17: Input Harmonics Control Using Non-Linear Capacitor in GaAs FET Power Amplifier
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OF1-18: Design of SAW Expander and Compressor on LiTaO₃ for a TCDMA Spread Spectrum System
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OF1-19: Simulation of Electromagnetic Effects of SAW RF Filters
 F.M. Pitschi, Siemens Matsushita Components, Munich, Germany, J.A. Nossek, Tech. Univ. Munich, Munich, Germany

OF1-20: High Frequency SAW Filter on Diamond
 K. Higaki, H. Nakahata, H. Kitabayashi, S. Fujii, K. Tanabe, Y. Seki, S. Shikata, Itami Research Labs., Sumitomo Elec. Ind., Ltd., Itami, Japan

OF1-21: A Sophisticated Design Procedure for a Triple Mode SAW Filter in Digital Mobile Telephones
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OF1-22: A Balanced-Type SAW Filter for PCN and PCS Systems
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OF1-23: 1/f Noise Modeling of InP HBT-Based Schottky Diodes for Monolithic Millimeter-Wave Mixers

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OF1-24: A Theoretical and Experimental Study on Low-Voltage Bias Controlled Oscillators

X. Zhang, Corp. R&D Ctr., J. Kramer, B. Rizzi, Semiconductor Business Unit, M/A-COM Inc., Lowell, MA

OF1-25: Fundamental Limitations on Output Power and Conversion Loss of Even Harmonic Mixers in Up-Conversion Operations

K. Itoh, K. Tajima, K. Kawakami, O. Ishida, K. Mizuno, Mitsubishi Elec. Corp., Kanagawa, Japan

OF1-26: On the Performance of Different HEMT Cryogenic Mixers

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OF1-27: A Simplified Method to Predict the Conversion Loss of FET Resistive Mixers

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OF1-28: Transistor Parameter Extraction Using DC, S-Parameter and Noise Data Simultaneously

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OF1-29: Improvements on a MOSFET Model for Non-Linear RF Simulations

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OF1-30: A Distributed, Measurement Based, Nonlinear Model of FETs for High Frequency Applications

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OF1-32: Novel Method for Determination of Junction-FET Access Resistances

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OF1-33: Nonlinear Modelling of SiGe HBTs up to 50 GHz

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OF1-34: A Bias Dependent HEMT Noise Model

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